IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PriorityApplication Serial No.09/444,024PriorityFiling DateNovember 19, 1999InventorJigish D. Trivedi et al.AssigneeMicron Technology, Inc.PriorityGroup Art Unit2811PriorityExaminerDouglas W. OwensAttorney's Docket No.MI22-1965Title:Integrated Circuitry

PRELIMINARY AMENDMENT

To:

Box Patent Application

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

D. Brent Kenady (Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

<u>AMENDMENTS</u>

In the Specification

At p. 1 before the "Technical Field" section, please insert the following:

RELATED PATENT DATA

This application resulted from a continuation application of U.S. Patent Application Serial No. 09/444,024, filed November 19, 1999, entitled "P-Type FET in a CMOS With Nitrogen Atoms in the Gate Dielectric", naming Jigish D. Trivedi, Zhongze Wang and Rhongsheng Yang as inventors, which was a divisional application of Patent Application Serial No. 09/386,076, filed August 30, 1999, now Patent No. 6,093,661, issued July 25, 2000, entitled "Integrated Circuitry and

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